

## Product Summary

$V_{(BR)DSS}$	$R_{DS(ON)}$ Max	$I_D$ Max $T_A = +25^\circ\text{C}$
30V	20m $\Omega$ @ $V_{GS} = 10\text{V}$	7.6A
	32m $\Omega$ @ $V_{GS} = 4.5\text{V}$	6.0A

## Description

This new generation MOSFET is designed to minimize the on-state resistance ( $R_{DS(ON)}$ ), yet maintain superior switching performance, making it ideal for high efficiency power management applications.

## Applications

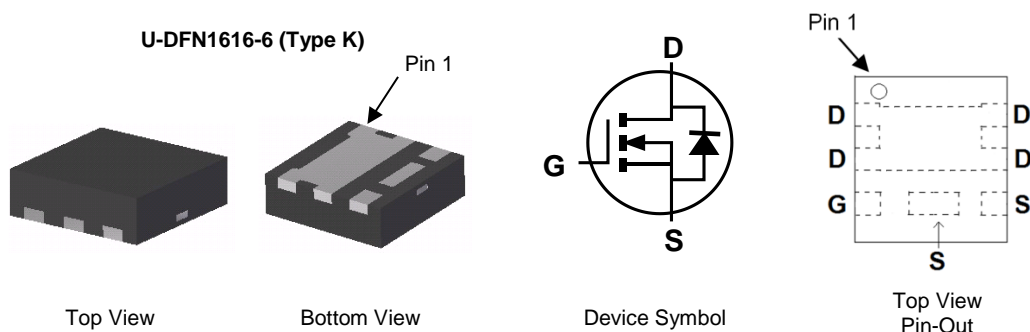
- Power Management Functions
- Loadswitch

## Features and Benefits

- Typical Off-Board Profile of 0.6mm – Ideally Suited for Thin Applications
- Low  $R_{DS(ON)}$  – Minimizes Conduction Losses
- PCB Footprint of 2.56mm<sup>2</sup>
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- Halogen and Antimony Free. "Green" Device (Note 3)**

## Mechanical Data

- Case: U-DFN1616-6 (Type K)
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Lead Free Plating (NiPdAu Finish over Copper Leadframe).
- Terminals: Solderable per MIL-STD-202, Method 208 <sup>(e4)</sup>
- Weight: 0.003 grams (Approximate)

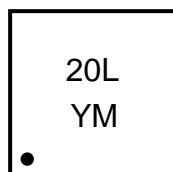


## Ordering Information (Note 4)

Product	Case	Packaging
DMT3020LFCL-7	U-DFN1616-6	3,000/Tape & Reel

- Notes:
- No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
  - See [http://www.diodes.com/quality/lead\\_free.html](http://www.diodes.com/quality/lead_free.html) for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  - Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  - For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

## Marking Information



20L = Product Type Marking Code  
 YM = Date Code Marking  
 Y = Year (ex: D = 2016)  
 M = Month (ex: 9 = September)

### Date Code Key

Year	2015	2016	2017	2018	2019	2020	2021
Code	C	D	E	F	G	H	I

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

**Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V <sub>DSS</sub>	30	V
Gate-Source Voltage	V <sub>GSS</sub>	±20	V
Continuous Drain Current (Note 6) V <sub>GS</sub> = 10V	I <sub>D</sub>	7.6 6.0	A
Pulsed Drain Current (Note 7)	I <sub>DM</sub>	40	A
Maximum Continuous Body Diode Forward Current (Note 6)	I <sub>S</sub>	2	A

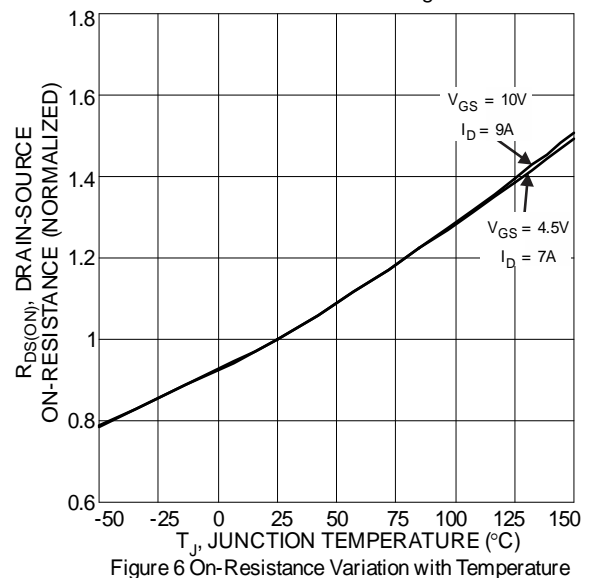
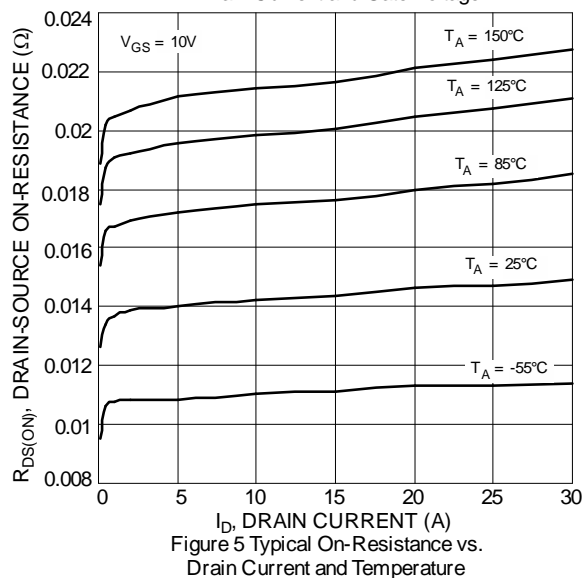
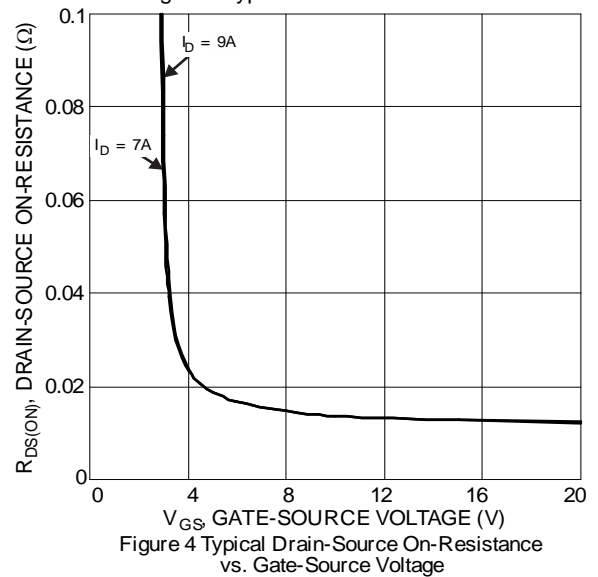
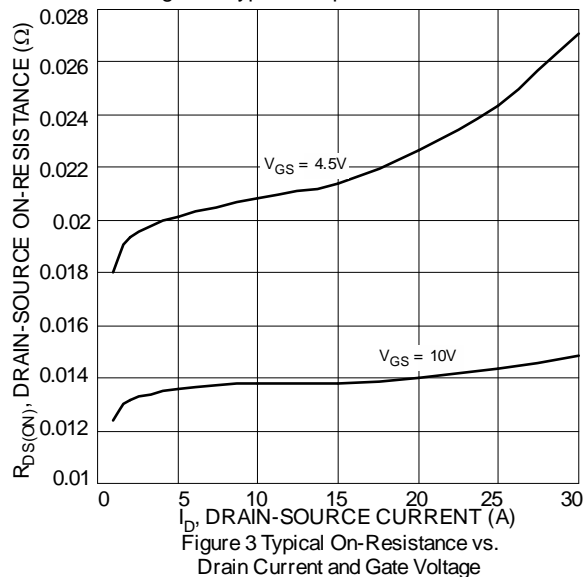
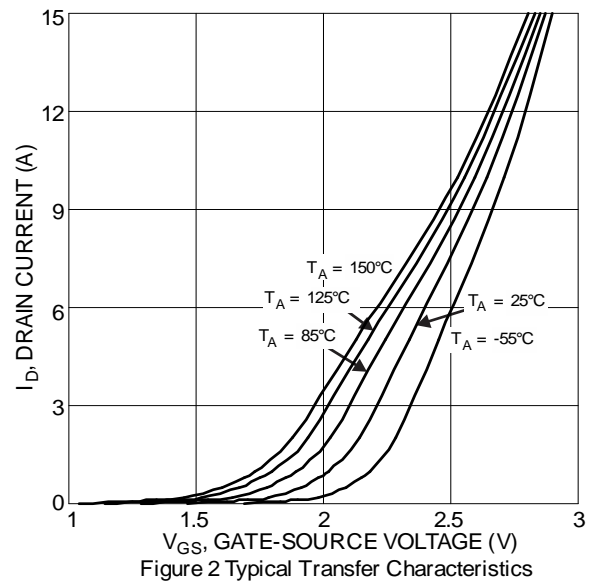
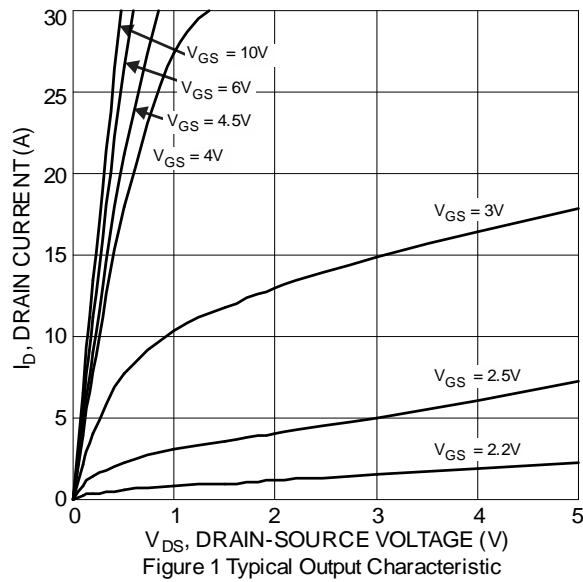
**Thermal Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

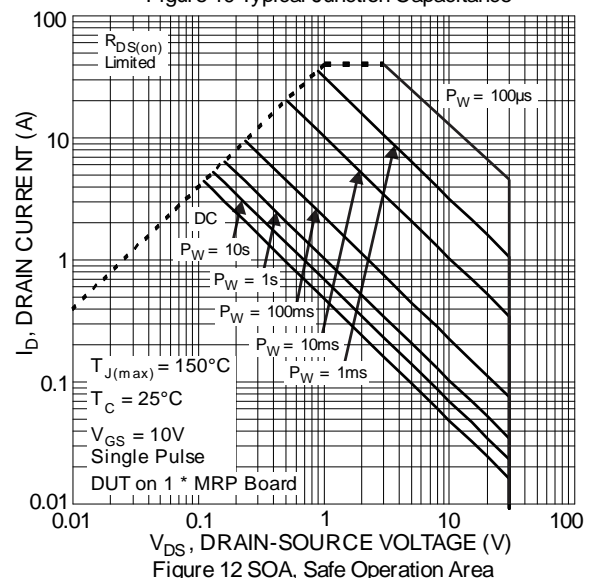
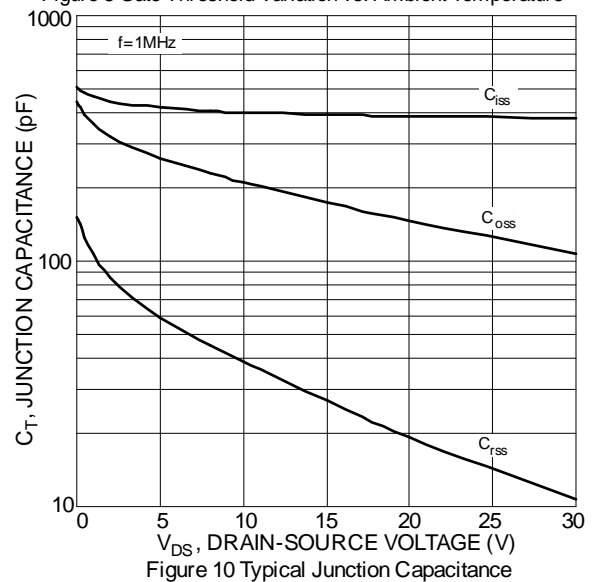
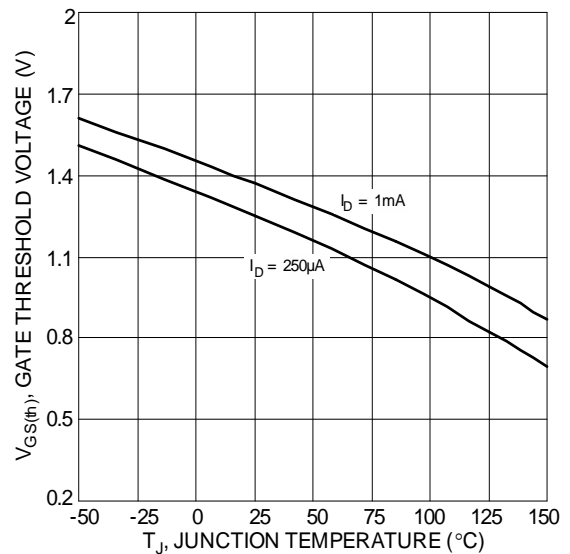
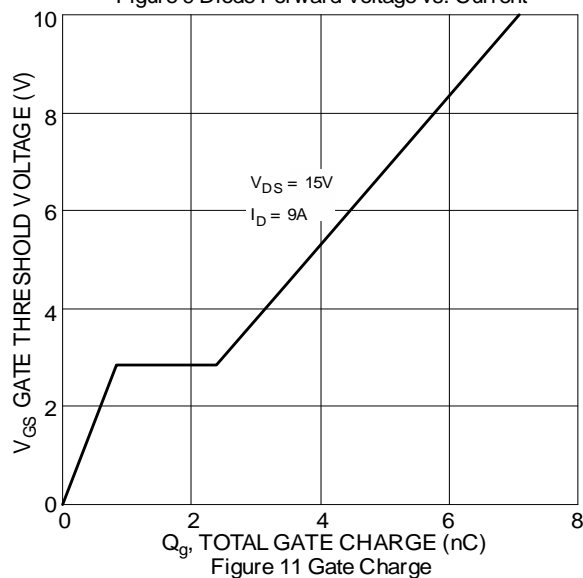
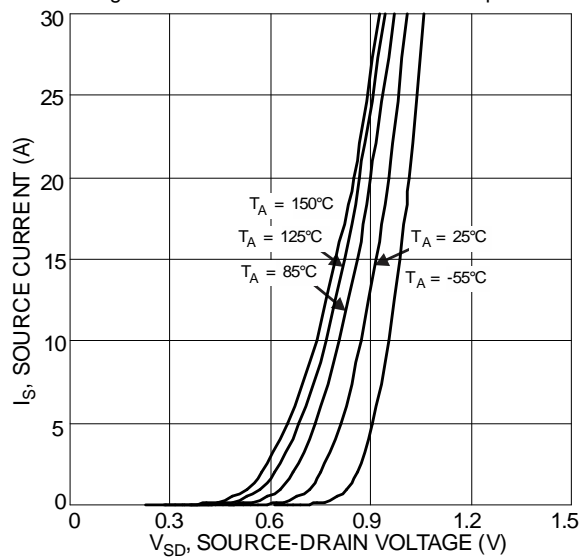
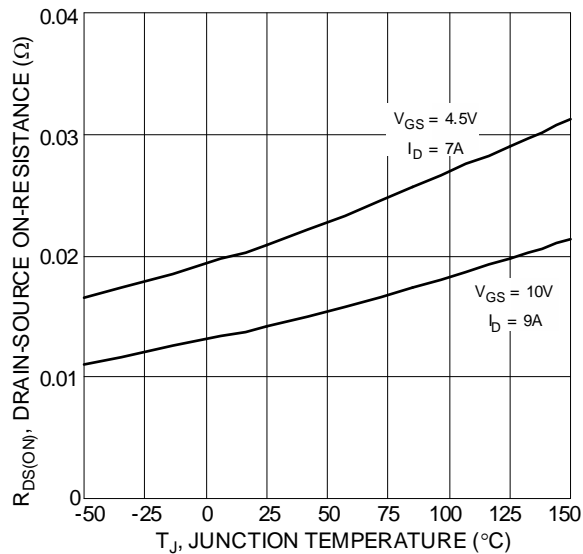
Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	P <sub>D</sub>	0.6	W
Thermal Resistance, Junction to Ambient (Note 5)	R <sub>θJA</sub>	207	°C/W
Power Dissipation (Note 6)	P <sub>D</sub>	1.7	W
Thermal Resistance, Junction to Ambient (Note 6)	R <sub>θJA</sub>	73	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

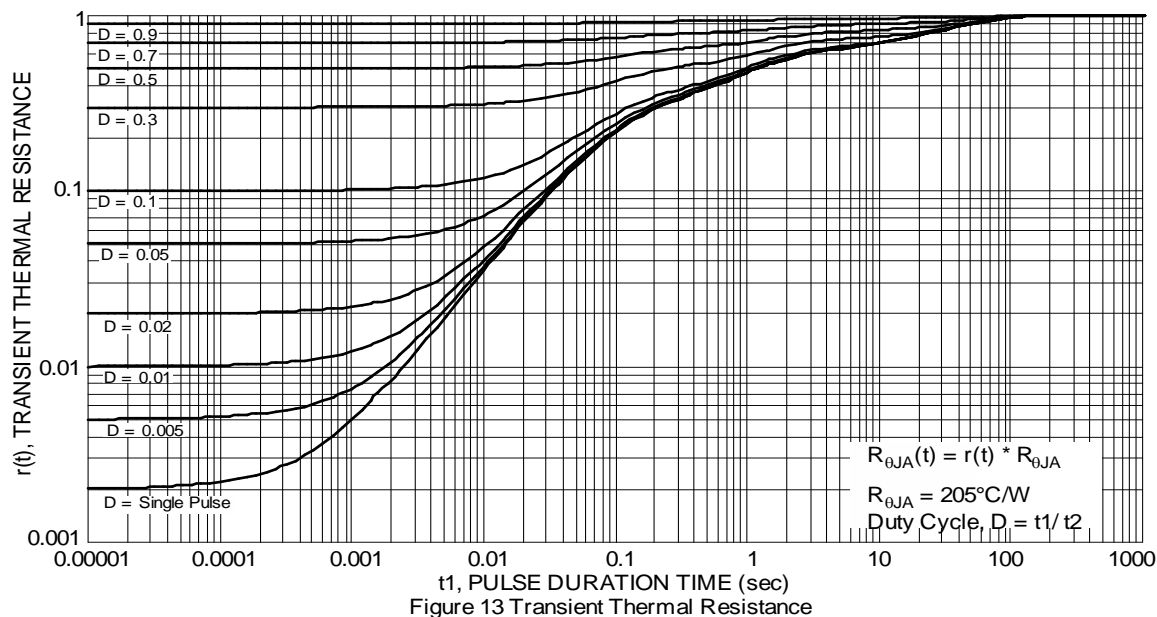
**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS</b> (Note 8)						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	30	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA
Zero Gate Voltage Drain Current T <sub>J</sub> = +25°C	I <sub>DSS</sub>	—	—	1.0	μA	V <sub>DS</sub> = 24V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	—	—	±100	nA	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS</b> (Note 8)						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	1	1.6	3.0	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	—	15 25	20 32	mΩ	V <sub>GS</sub> = 10V, I <sub>D</sub> = 9A V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 7A
Diode Forward Voltage	V <sub>SD</sub>	—	0.78	1.0	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 2A
<b>DYNAMIC CHARACTERISTICS</b> (Note 9)						
Input Capacitance	C <sub>ISS</sub>	—	393	—	pF	V <sub>DS</sub> = 15V, V <sub>GS</sub> = 0V, f = 1.0MHz
Output Capacitance	C <sub>OSS</sub>	—	173	—	pF	
Reverse Transfer Capacitance	C <sub>RSS</sub>	—	27	—	pF	
Gate Resistance	R <sub>G</sub>	—	1.1	—	Ω	V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1MHz
Total Gate Charge (V <sub>GS</sub> = 10V)	Q <sub>G</sub>	—	7.0	—	nC	V <sub>DS</sub> = 15V, I <sub>D</sub> = 9A
Total Gate Charge (V <sub>GS</sub> = 4.5V)	Q <sub>G</sub>	—	3.6	—	nC	
Gate-Source Charge	Q <sub>GS</sub>	—	0.9	—	nC	
Gate-Drain Charge	Q <sub>GD</sub>	—	1.5	—	nC	
Turn-On Delay Time	t <sub>D(ON)</sub>	—	1.8	—	ns	V <sub>DD</sub> = 15V, V <sub>GS</sub> = 10V, I <sub>D</sub> = 9A R <sub>G</sub> = 6Ω
Turn-On Rise Time	t <sub>R</sub>	—	1.9	—	ns	
Turn-Off Delay Time	t <sub>D(OFF)</sub>	—	7.5	—	ns	
Turn-Off Fall Time	t <sub>F</sub>	—	2.4	—	ns	I <sub>F</sub> = 9A, dI/dt = 100A/μs
Body Diode Reverse Recovery Time	t <sub>RR</sub>	—	10	—	ns	
Body Diode Reverse Recovery Charge	Q <sub>RR</sub>	—	2.6	—	nC	

- Notes:
- Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
  - Device mounted on FR-4 substrate PC board, 2oz copper, with 1-inch square copper plate.
  - Repetitive rating, pulse width limited by junction temperature.
  - Short duration pulse test used to minimize self-heating effect.
  - Guaranteed by design. Not subject to product testing.
  - I<sub>AS</sub> and E<sub>AS</sub> rating are based on low frequency and duty cycles to keep T<sub>J</sub> = +25°C.



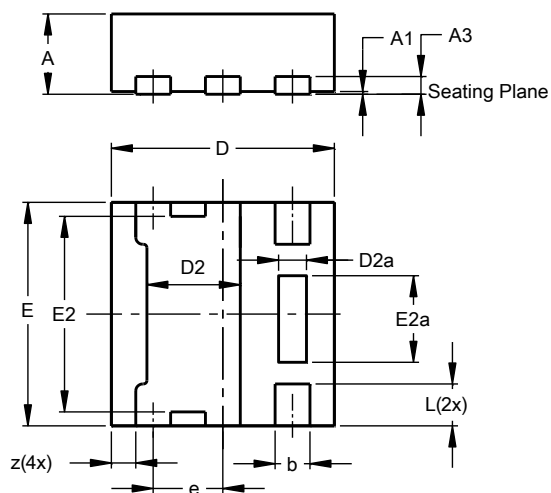




## Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

U-DFN1616-6 (Type K)

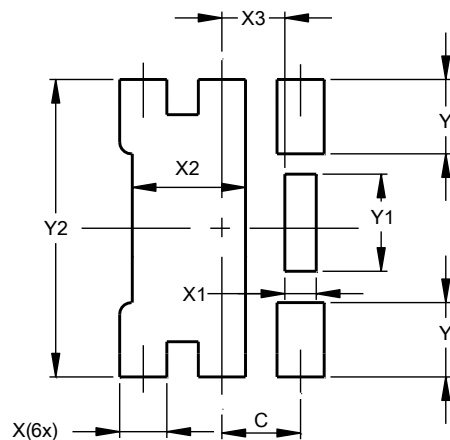


U-DFN1616-6 (Type K)			
Dim	Min	Max	Typ
A	0.55	0.60	0.575
A1	0.00	0.05	0.02
A3	—	—	0.13
b	0.20	0.30	0.25
D	1.55	1.65	1.60
D2	0.57	0.77	0.67
D2a	0.10	0.30	0.20
e	—	—	0.50
E	1.55	1.65	1.60
E2	1.30	1.50	1.40
E2a	0.52	0.72	0.62
L	0.25	0.35	0.30
z	—	—	0.175
All Dimensions in mm			

## Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

U-DFN1616-6 (Type K)



Dimensions	Value (in mm)
C	0.500
X	0.300
X1	0.200
X2	0.720
X3	0.400
Y	0.475
Y1	0.620
Y2	1.900

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